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SangBum Kim received the B.S. degree from Seoul National University, Seoul, Korea, in 2001 and the M.S. and Ph.D. degrees from Stanford University, Stanford, CA, in 2005 and 2010, respectively, all in electrical engineering. His Ph.D. dissertation focused on the scalability and reliability of phase change memory (PCM) including scaling rule analysis, germanium nanowire diode as a scalable selection device, and study of thermal disturbance, drift, and threshold switching using micro thermal stage.

Since he joined the IBM T. J. Watson Research Center in 2010, he has been working on phase change memory devices for various memory applications such as storage-class memory, embedded memory, and brain-inspired neuromorphic computing. He is currently a Research Staff Member with the IBM T. J. Watson Research Center.